

CSD18532Q5B 60V N 通道 NexFET™ 功率金属氧化物半导体场效应晶体管 (MOSFET)

1 特性

- 超低 Q_g 和 Q_{gd}
- 低热阻
- 雪崩额定值
- 逻辑电平
- 无铅引脚镀层
- 符合 RoHS 标准
- 无卤素
- SON 5mm × 6mm 塑料封装

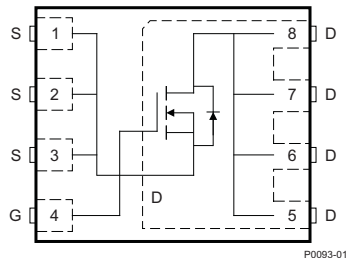
2 应用

- 直流 - 直流转换
- 次级侧同步整流器
- 隔离式转换器主级侧开关
- 电机控制

3 说明

这款采用 5mm × 6mm SON 封装的 2.5mΩ、60V NexFET™ 功率 MOSFET 旨在用于最大程度降低功率转换应用中的损耗。

俯视图



P0093-01

产品概要

$T_A = 25^\circ\text{C}$		典型值	单位
V_{DS}	漏源电压	60	V
Q_g	栅极电荷总量 (10V)	44	nC
Q_{gd}	栅极电荷 (栅极到漏极)	6.9	nC
$R_{DS(on)}$	漏源导通电阻	$V_{GS} = 4.5\text{V}$	3.3
		$V_{GS} = 10\text{V}$	2.5
$V_{GS(th)}$	阈值电压	1.8	V

器件信息(1)

器件	数量	包装介质	封装	发货
CSD18532Q5B	2500	13 英寸卷带	SON	卷带封装
CSD18532Q5BT	250	13 英寸卷带	5.00-mm × 6.00-mm 塑料封装	

(1) 如需了解所有可用封装, 请参阅数据表末尾的可订购产品附录。

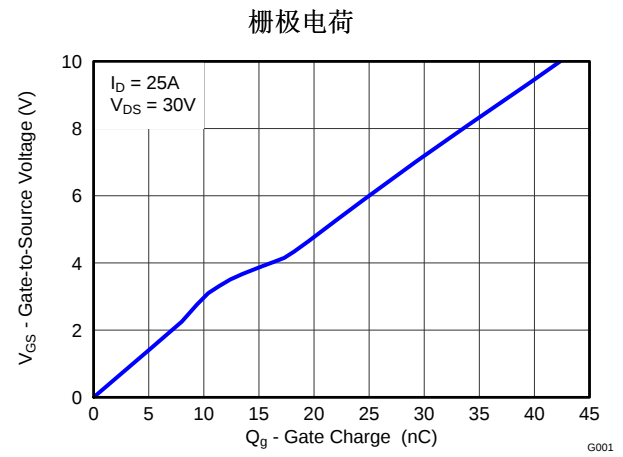
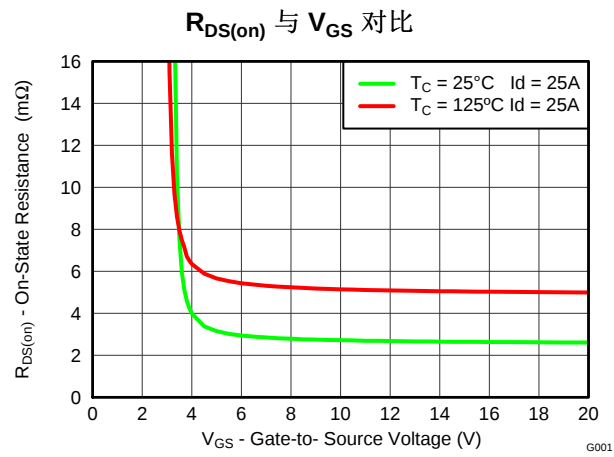
绝对最大额定值

$T_A = 25^\circ\text{C}$		值	单位
V_{DS}	漏源电压	60	V
V_{GS}	栅源电压	±20	V
I_D	持续漏极电流 (受封装限制)	100	A
	持续漏极电流 (受芯片限制), $T_C = 25^\circ\text{C}$ 时测得	172	
	持续漏极电流(1)	23	
I_{DM}	脉冲漏极电流(2)	400	A
P_D	功率耗散(1)	3.2	W
	功耗, $T_C = 25^\circ\text{C}$	156	
T_J, T_{stg}	工作结温、储存温度	-55 至 150	°C
E_{AS}	雪崩能量, 单一脉冲 $I_D = 80\text{A}$, $L = 0.1\text{mH}$, $R_G = 25\Omega$	320	mJ

(1) $R_{\theta JA} = 40^\circ\text{C/W}$, 这是在一块厚度为 0.06 英寸环氧树脂 (FR4) 印刷电路板 (PCB) 上的 1 英寸², 2 盎司铜焊盘上测得的典型值。

(2) 最大 $R_{\theta JC} = 0.8^\circ\text{C/W}$, 脉冲持续时间 $\leq 100\mu\text{s}$, 占空比 $\leq 1\%$ 。





目录

1	特性	1	6.1	接收文档更新通知	8
2	应用	1	6.2	社区资源	8
3	说明	1	6.3	商标	8
4	修订历史记录	3	6.4	静电放电警告	8
5	Specifications	4	6.5	Glossary	8
	5.1 Electrical Characteristics	4	7	机械、封装和可订购信息	9
	5.2 Thermal Information	4	7.1	Q5B 封装尺寸	9
	5.3 Typical MOSFET Characteristics	5	7.2	建议 PCB 布局	10
6	器件和文档支持	8	7.3	建议模板布局	10
			7.4	Q5B 卷带信息	11

4 修订历史记录

Changes from Revision C (May 2017) to Revision D Page

- Extended the V_{DS} on [Figure 5](#) to 60 V. **5**

Changes from Revision B (July 2014) to Revision C Page

- 已添加 “接收文档更新通知”和“社区资源”部分添加到了“器件和文档支持”。 **8**
- 已更改 将“建议 PCB 布局”部分方框图中 **10**

Changes from Revision A (May 2014) to Revision B Page

- 将“7 英寸卷带”更改成了“13 英寸卷带”。 **1**

Changes from Original (Nov 2012) to Revision A Page

- 更新了器件 说明添加了 ESD 信息。 **1**
- 指定了 10V 时的 Q_g 。 **1**
- 添加了小卷带选项。 **1**
- 将脉冲漏极电流增至 400A。 **1**
- 添加了表示外壳温度保持在 25°C 时的最大功耗的行。 **1**
- 更新了脉冲漏极电流条件。 **1**
- Eliminated Q_g at 4.5 V. **4**
- Changed [Figure 1](#) from a normalized $R_{\theta JA}$ curve to a $R_{\theta JC}$ curve..... **5**
- Updated the safe operating area in [Figure 10](#). **7**
- 更新了机械制图。 **9**

5 Specifications

5.1 Electrical Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise stated

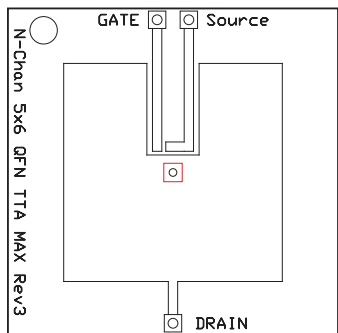
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV _{DSS}	Drain-to-source voltage	V _{GS} = 0 V, I _D = 250 μA	60			V
I _{DSS}	Drain-to-source leakage current	V _{GS} = 0 V, V _{DS} = 48 V			1	μA
I _{GSS}	Gate-to-source leakage current	V _{DS} = 0 V, V _{GS} = 20 V			100	nA
V _{GS(th)}	Gate-to-source threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	1.5	1.8	2.2	V
R _{DS(on)}	Drain-to-source on-resistance	V _{GS} = 4.5 V, I _D = 25 A	3.3		4.3	mΩ
		V _{GS} = 10 V, I _D = 25 A	2.5		3.2	
g _{fs}	Transconductance	V _{DS} = 30 V, I _D = 25 A	143			S
DYNAMIC CHARACTERISTICS						
C _{iss}	Input capacitance	V _{GS} = 0 V, V _{DS} = 30 V, f = 1 MHz		3900	5070	pF
C _{oss}	Output capacitance			470	611	pF
C _{rss}	Reverse transfer capacitance			13	17	pF
R _G	Series gate resistance			1.2	2.4	Ω
Q _g	Gate charge total (10 V)	V _{DS} = 30 V, I _D = 25 A		44	58	nC
Q _{gd}	Gate charge gate-to-drain			6.9		nC
Q _{gs}	Gate charge gate-to-source			10		nC
Q _{g(th)}	Gate charge at V _{th}			6.3		nC
Q _{oss}	Output charge	V _{DS} = 30 V, V _{GS} = 0 V		52		nC
t _{d(on)}	Turnon delay time	V _{DS} = 30 V, V _{GS} = 10 V, I _{DS} = 25 A, R _G = 0 Ω		5.8		ns
t _r	Rise time			7.2		ns
t _{d(off)}	Turnoff delay time			22		ns
t _f	Fall time			3.1		ns
DIODE CHARACTERISTICS						
V _{SD}	Diode forward voltage	I _{SD} = 25 A, V _{GS} = 0 V		0.8	1	V
Q _{rr}	Reverse recovery charge	V _{DS} = 30 V, I _F = 25 A, di/dt = 300 A/μs		111		nC
t _{rr}	Reverse recovery time			49		ns

5.2 Thermal Information

 $T_A = 25^\circ\text{C}$ unless otherwise stated

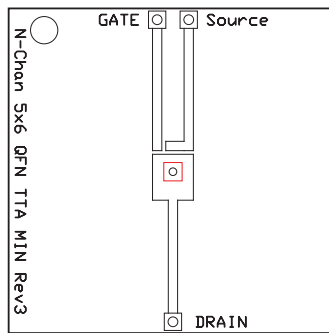
THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case thermal resistance ⁽¹⁾			0.8	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽¹⁾⁽²⁾			50	$^\circ\text{C}/\text{W}$

- $R_{\theta JC}$ is determined with the device mounted on a 1-in² (6.45-cm²), 2-oz. (0.071-mm) thick Cu pad on a 1.5-in $\times$ 1.5-in (3.81-cm $\times$ 3.81-cm), 0.06-in (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
- Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.



M0137-01

Max $R_{\theta JA} = 50^{\circ}\text{C/W}$
when mounted on 1 in²
(6.45 cm²) of
2-oz (0.071-mm) thick
Cu.

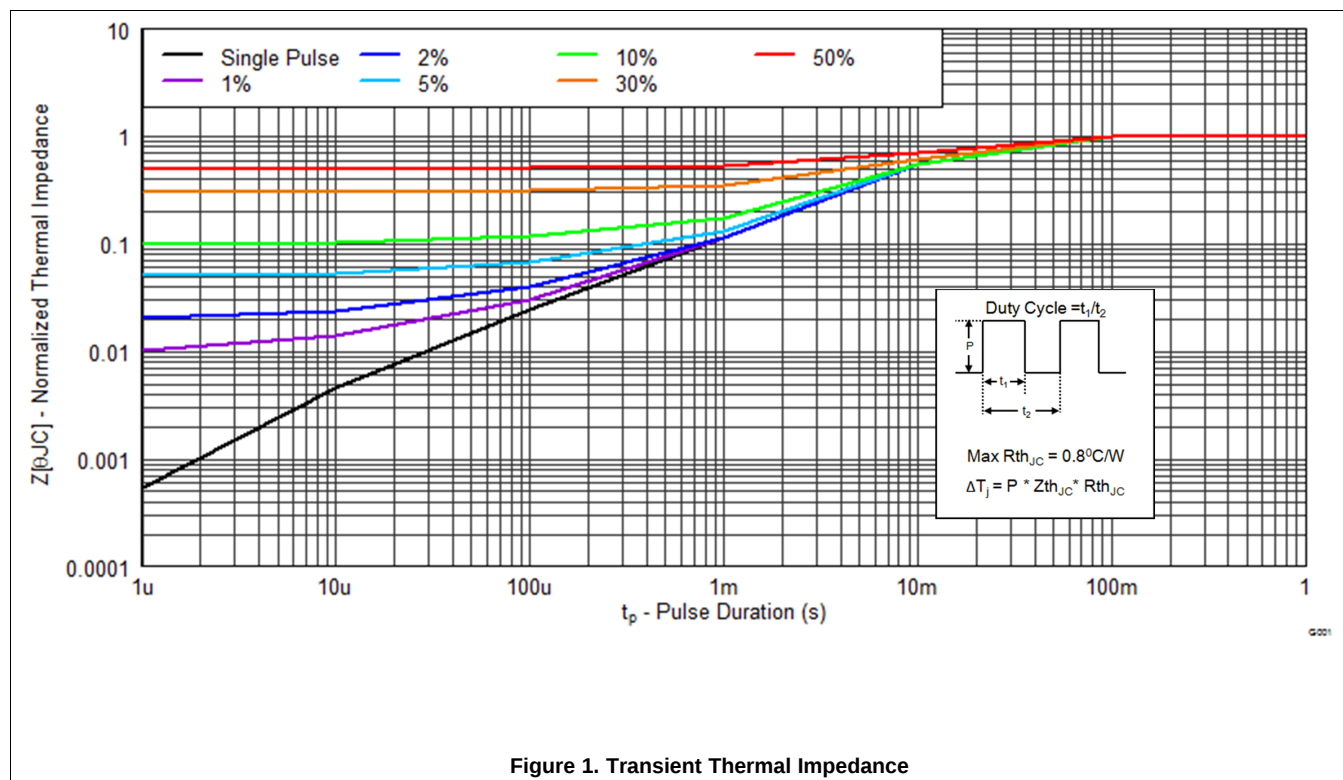


M0137-02

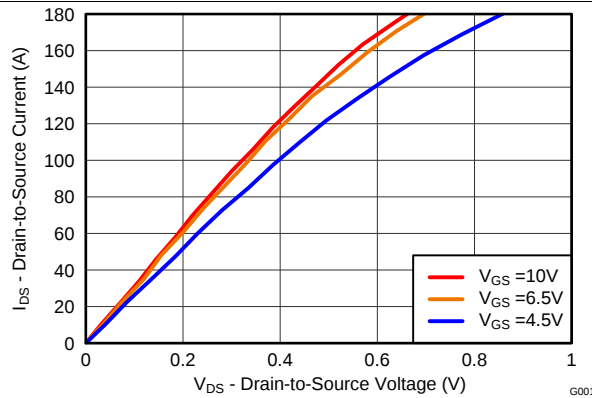
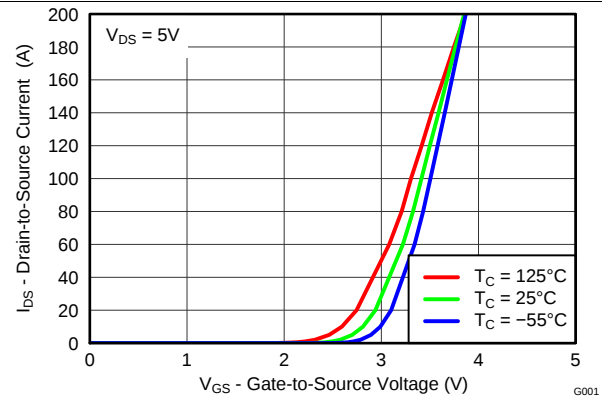
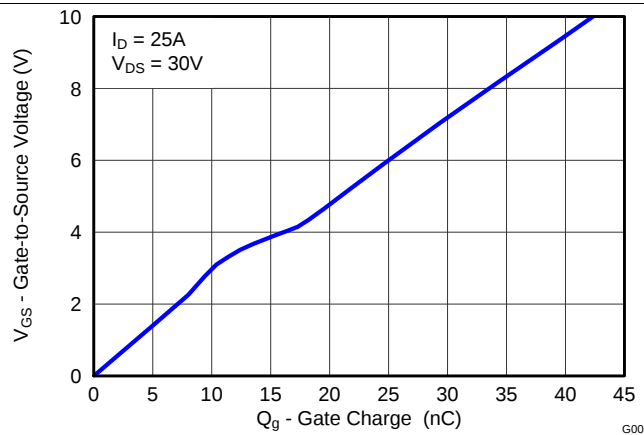
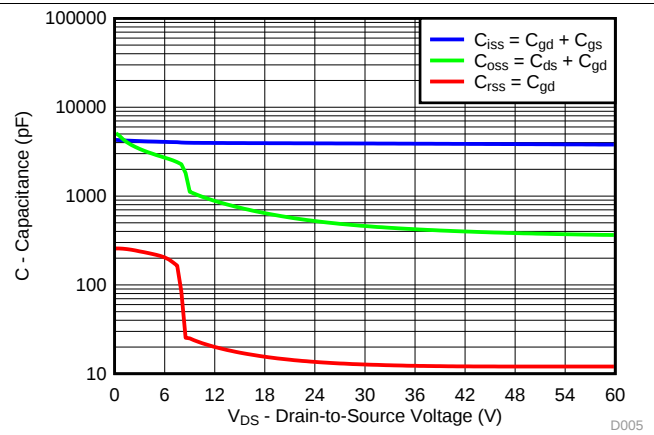
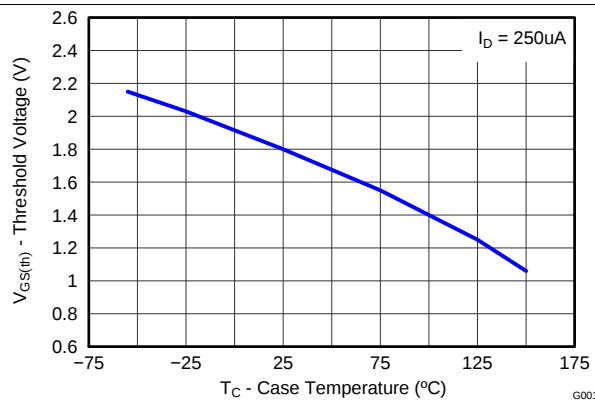
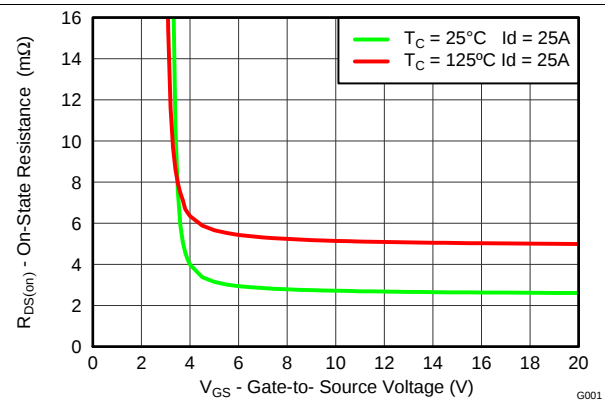
Max $R_{\theta JA} = 125^{\circ}\text{C/W}$
when mounted on a
minimum pad area of
2-oz (0.071-mm) thick
Cu.

5.3 Typical MOSFET Characteristics

$T_A = 25^{\circ}\text{C}$ unless otherwise stated



Typical MOSFET Characteristics (continued)

 $T_A = 25^\circ\text{C}$ unless otherwise stated

Figure 2. Saturation Characteristics

Figure 3. Transfer Characteristics

Figure 4. Gate Charge

Figure 5. Capacitance

Figure 6. Threshold Voltage vs Temperature

Figure 7. On-State Resistance vs Gate-to-Source Voltage

Typical MOSFET Characteristics (continued)

$T_A = 25^\circ\text{C}$ unless otherwise stated

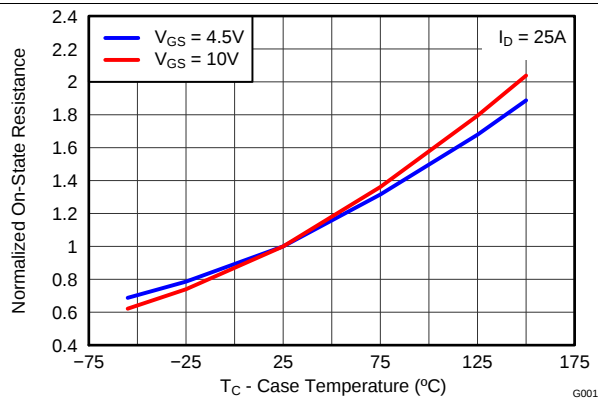


Figure 8. Normalized On-State Resistance vs Temperature

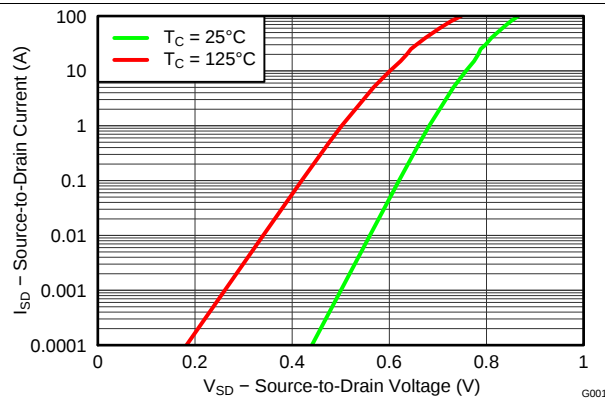


Figure 9. Typical Diode Forward Voltage

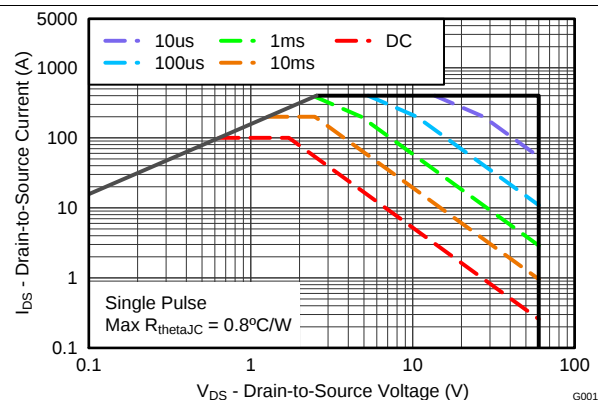


Figure 10. Maximum Safe Operating Area

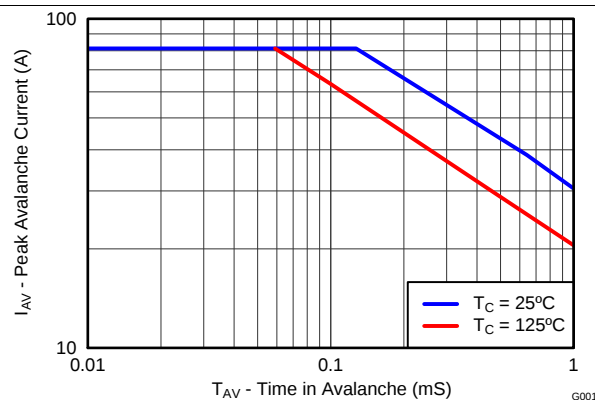


Figure 11. Single Pulse Unclamped Inductive Switching

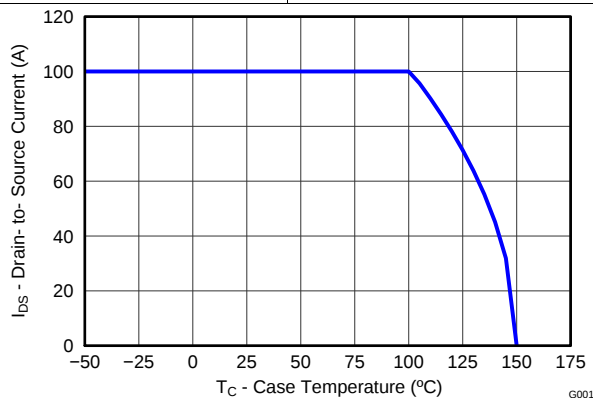


Figure 12. Maximum Drain Current vs Temperature

6 器件和文档支持

6.1 接收文档更新通知

要接收文档更新通知，请导航至 TI.com 上的器件产品文件夹。请单击右上角的提醒我 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

6.2 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

TI E2E™ 在线社区 [TI 的工程师对工程师 \(E2E\) 社区](http://e2e.ti.com)。此社区的创建目的在于促进工程师之间的协作。在 e2e.ti.com 中，您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。

设计支持 [TI 参考设计支持](#) 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

6.3 商标

NexFET, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

6.4 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

6.5 Glossary

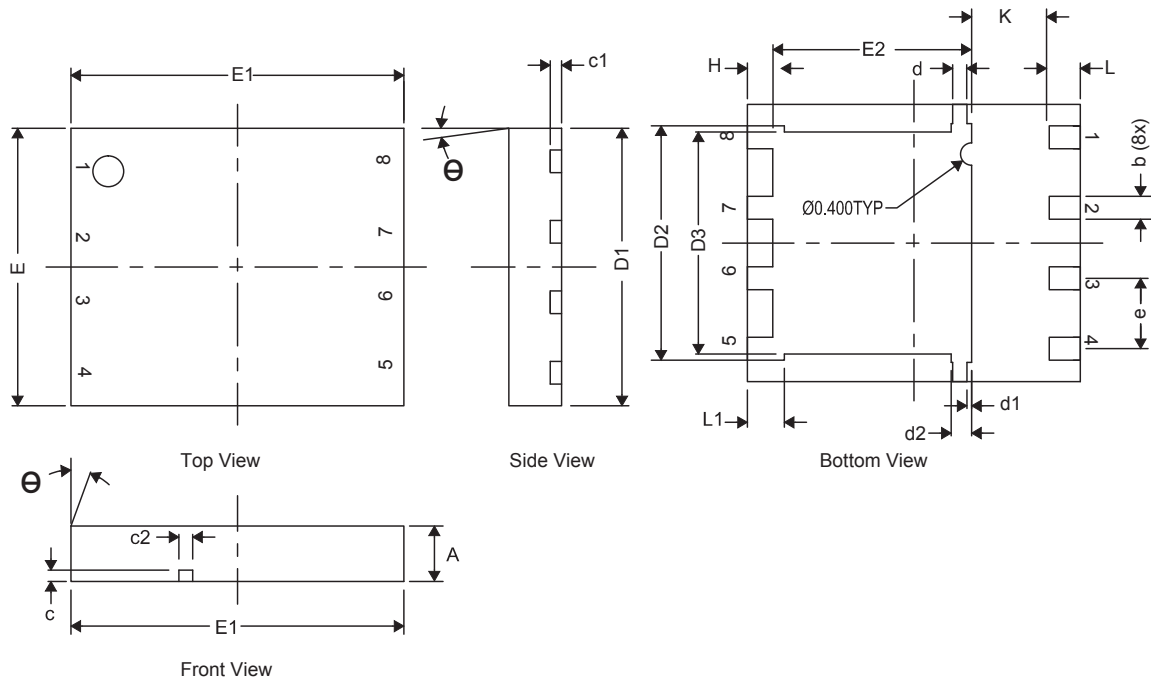
[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

7 机械、封装和可订购信息

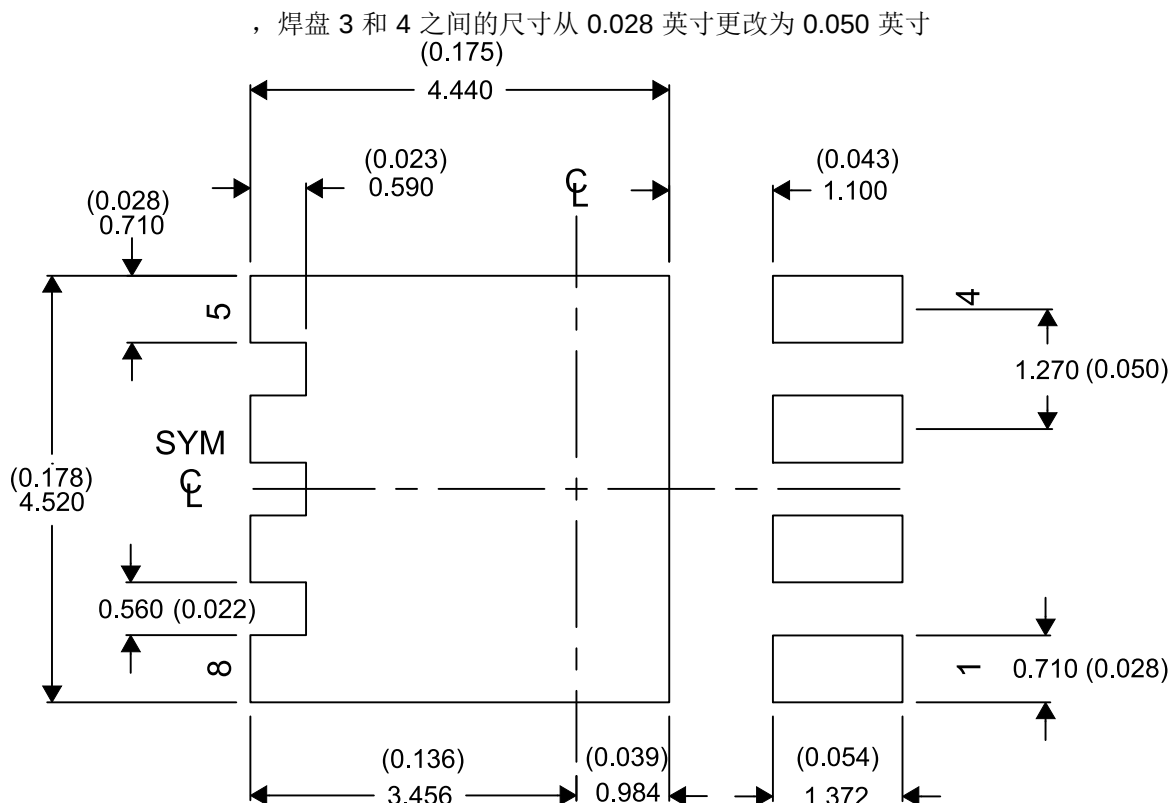
以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知和修订此文档。如欲获取此数据表的浏览器版本，请参阅左侧的导航。

7.1 Q5B 封装尺寸



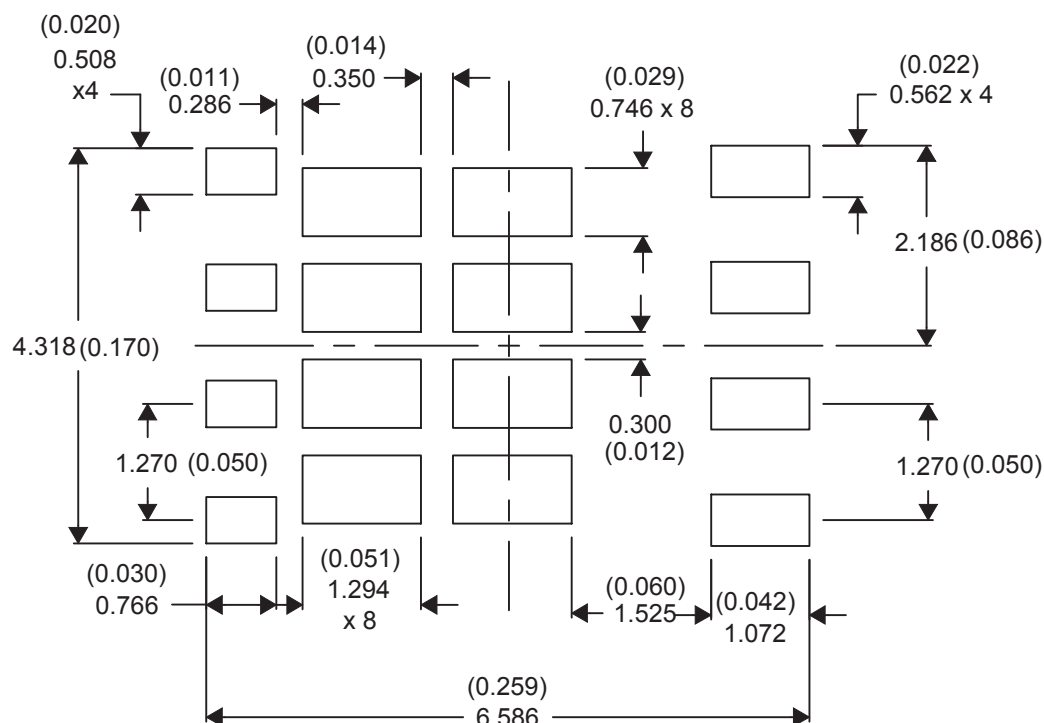
DIM	毫米		
	最小值	标称值	最大值
A	0.80	1.00	1.05
b	0.36	0.41	0.46
c	0.15	0.20	0.25
c1	0.15	0.20	0.25
c2	0.20	0.25	0.30
D1	4.90	5.00	5.10
D2	4.12	4.22	4.32
D3	3.90	4.00	4.10
d	0.20	0.25	0.30
d1	0.085 典型值		
d2	0.319	0.369	0.419
E	4.90	5.00	5.10
E1	5.90	6.00	6.10
E2	3.48	3.58	3.68
e	1.27 典型值		
H	0.36	0.46	0.56
L	0.46	0.56	0.66
L1	0.57	0.67	0.77
θ	0°	—	—
K	1.40 典型值		

7.2 建议 PCB 布局

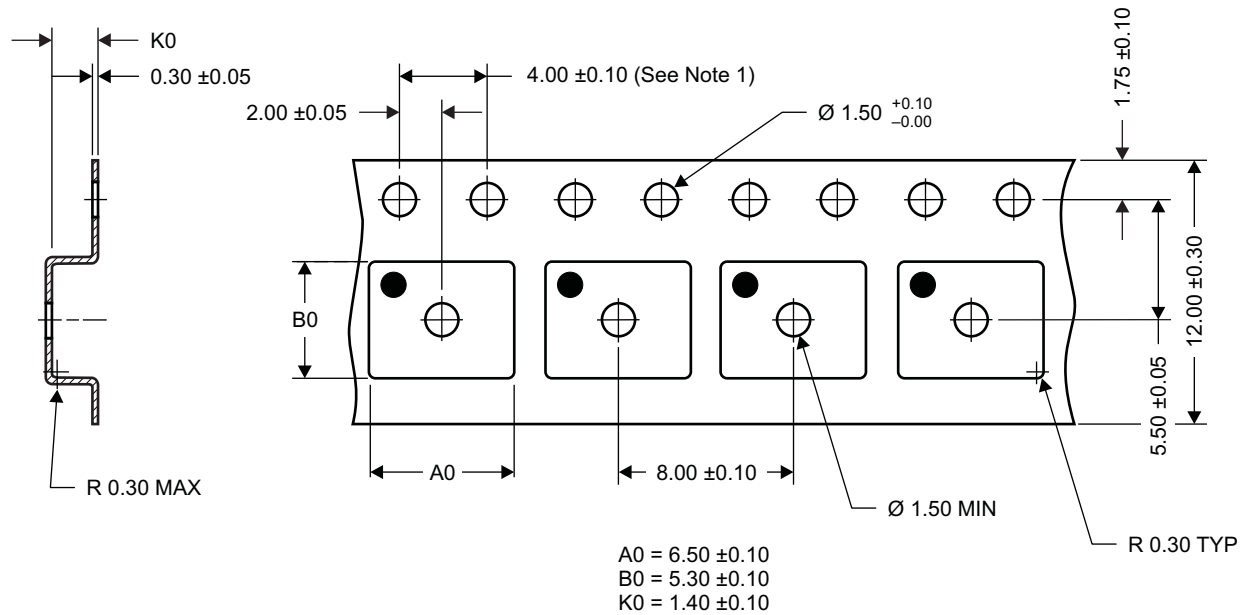


如需了解针对 PCB 设计的建议电路布局，请参阅《通过 PCB 布局技巧来减少振铃》(SLPA005)。

7.3 建议模板布局



7.4 Q5B 卷带信息



M0138-01

注释:

- 10 个链齿孔的累积容差为 ± 0.2 。
- 每 100mm 长度的翘曲不能超过 1mm，在 250mm 长度上不累积。
- 材料：黑色抗静电聚苯乙烯
- 所有尺寸单位均为 mm（除非另外注明）。
- 高于孔眼底部 0.3mm 的平面上测量得到 $A0$ 和 $B0$ 值。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CSD18532Q5B	Active	Production	VSON-CLIP (DNK) 8	2500 LARGE T&R	ROHS Exempt	NIPDAU SN	Level-1-260C-UNLIM	-55 to 150	CSD18532
CSD18532Q5B.B	Active	Production	VSON-CLIP (DNK) 8	2500 LARGE T&R	ROHS Exempt	NIPDAU	Level-1-260C-UNLIM	-55 to 150	CSD18532
CSD18532Q5BG4	Active	Production	VSON-CLIP (DNK) 8	2500 LARGE T&R	ROHS Exempt	NIPDAU	Level-1-260C-UNLIM	-55 to 150	CSD18532
CSD18532Q5BG4.B	Active	Production	VSON-CLIP (DNK) 8	2500 LARGE T&R	ROHS Exempt	NIPDAU	Level-1-260C-UNLIM	-55 to 150	CSD18532
CSD18532Q5BT	Active	Production	VSON-CLIP (DNK) 8	250 SMALL T&R	ROHS Exempt	NIPDAU SN	Level-1-260C-UNLIM	-55 to 150	CSD18532
CSD18532Q5BT.B	Active	Production	VSON-CLIP (DNK) 8	250 SMALL T&R	ROHS Exempt	NIPDAU	Level-1-260C-UNLIM	-55 to 150	CSD18532

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

重要通知和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做任何明示或暗示的担保，包括但不限于对适销性、与某特定用途的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他安全、安保法规或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的相关应用。严禁以其他方式对这些资源进行复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。对于因您对这些资源的使用而对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，您将全额赔偿，TI 对此概不负责。

TI 提供的产品受 [TI 销售条款](#)、[TI 通用质量指南](#) 或 [ti.com](#) 上其他适用条款或 TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。除非德州仪器 (TI) 明确将某产品指定为定制产品或客户特定产品，否则其产品均为按确定价格收入目录的标准通用器件。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

版权所有 © 2025，德州仪器 (TI) 公司

最后更新日期：2025 年 10 月